

Title of Change:	Transfer of DSN2 Schottky plating site (from FCMS, China to HTKS, China) & Back End sites consolidation (from JCAP, ONSC, SBN to JCAP, ONSC)
Proposed First Ship date:	01 Jan 2024 or earlier if approved by customer
Contact Information:	Contact your local onsemi Sales Office or NurulAliaFatin.Redzoan@onsemi.com
PCN Samples Contact:	Contact your local onsemi Sales Office. Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.
Type of Notification:	This is an Initial Product/Process Change Notification (IPCN) sent to customers. An IPCN is an advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan. The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN). This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 90 days prior to implementation of the change. In case of questions, contact < PCN.Support@onsemi.com >
Marking of Parts/ Traceability of Change:	Affected products will be identified by date code
Change Category:	Test Change, Assembly Change, Wafer Fab Change
Change Sub-Category(s):	Material Change, Manufacturing Process Change, Manufacturing Site Transfer

Sites Affected:

onsemi Sites	External Foundry/Subcon Sites
onsemi Shenzhen, China	Huatian Technology, China
onsemi, ISMF Malaysia	JCAP, China

Description and Purpose:

onsemi is notifying its customers of its intent to transfer the plating site and consolidate the backed sites of its DSN2 Schottky portfolio. The change will include the transfer of plating site from external foundry facility, Flipchip Millenium (FCMS), China to external foundry facility, Huatian Technology (HTKS), China. Additionally, the back-end sites will be consolidated to onsemi Shenzhen, China and JCET Jiangyn (AVM) (JCAP), China. Other changes include a standardization of die top metal and standardization of product marking. Refer to the below table for details of changes by OPN:

	Before Change Description	After Change Description
Background Site	onsemi ISMF, Malaysia	Huatian Technology, China
Front Metal	20kAlSiCu, 40kAlSi	20kAlSiCu
Marking Design	<p>MARKING DIAGRAMS</p> <p>PIN 1</p> <p>05F40 YYY</p> <p>DSN2 (0402) CASE 152AC</p> <p>05F40 = Specific Device Code YYY = Year Code</p>	<p>PIN 1</p> <p>ACM</p> <p>DSN2 (0402) CASE 152AC</p> <p>AC = Specific Device Code M = Month Code</p>

	<p>DSN2 (0402) CASE 152AC</p> <p>AC = Specific Device Code M = Month Code</p>	
Plating Site	Flipchip Millenium (Shanghai)(FCMS), China JS Foundry, Japan	Huantian Technology, China
Probe, Tape & Reel Site	onsemi Seremban, Malaysia onsemi Shenzhen, China JCET Jiangyn BE(AVM)(JCAP), China	onsemi Shenzhen, China JCET Jiangyn BE(AVM)(JCAP), China

NOTE: Change table is attached.

To view attachments:

1. Download pdf copy of the PCN to your computer
2. Open the downloaded pdf copy of the PCN
3. Click on the paper clip icon available on the menu provided in the left/bottom portion of the screen to reveal the Attachment field
4. Then click on the attached file/s



IPCN FCMS TO HTKS
changes tables.pdf

Qualification Plan:

QV DEVICE NAME: NSVR05F40NXT5G

RMS: S89608

PACKAGE: FC SCHOTTKY DIODE 0402

Test	Specification	Condition	Interval
High Temperature Storage Life	JESD22-A103	Ta= 150°C	1008 hrs
Preconditioning	J-STD-020 JESD-A113	MSL 1 @ 260 °C	
Temperature Cycling	JESD22-A104	Ta= -40°C to +125°C	850 cyc
Unbiased Highly Accelerated Stress Test	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs

QV DEVICE NAME: SNSR01F30NXT5G

RMS: S89606

PACKAGE: FC SCHOTTKY DIODE 0201

Test	Specification	Condition	Interval
High Temperature Storage Life	JESD22-A103	Ta= 150°C	1008 hrs
Preconditioning	J-STD-020 JESD-A113	MSL 1 @ 260 °C	
Temperature Cycling	JESD22-A104	Ta= -40°C to +125°C	850 cyc
Unbiased Highly Accelerated Stress Test	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs



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Issue Date: 11 Apr 2023

QV DEVICE NAME: NSR20F40NXT5G

RMS: S89629

PACKAGE: FC SCHOTTKY DIODE 0603

Test	Specification	Condition	Interval
High Temperature Storage Life	JESD22-A103	Ta= 150°C	1008 hrs
Preconditioning	J-STD-020 JESD-A113	MSL 1 @ 260 °C	
Temperature Cycling	JESD22-A104	Ta= -40°C to +125°C	850 cyc
Unbiased Highly Accelerated Stress Test	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs

Estimated date for qualification completion: WW30

Electrical Characteristics Summary:

Electrical characteristics are not impacted.

List of Affected Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the [**PCN Customized Portal**](#).

Part Number	Qualification Vehicle
SNSR15304NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
SNSR20F30WCNXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
SNSR20F30WC1NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
SNSR20F20NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
NSR20F40NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
NSR20F30NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
NSR20F20NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
NSR10F40NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
NSR10F30NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
NSR10F20NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
SNSR05F40NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
NSR05F40NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
NSR05F30NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
NSR05F20NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
SNSR01F30NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
NSR02L30NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
NSR02F30NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G



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NSR01L30NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G
NSR01F30NXT5G	SNSR01F30NXT5G, NSR20F40NXT5G